

DMTH45M5LPDW-VB Datasheet

Dual N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
40	0.0055 at $V_{GS} = 10$ V	60	20 nC
	0.0065 at $V_{GS} = 4.5$ V	45	

FEATURES

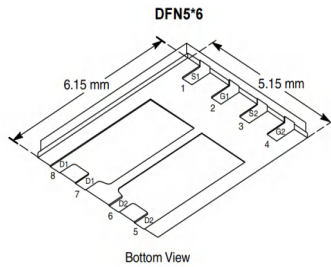
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % UIS Tested
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



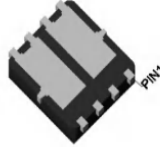
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

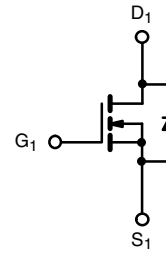
- Set Top Box
- Low Current DC/DC



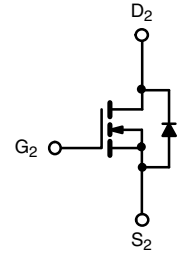
Top View



Bottom View



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	60 ^a	A
	$T_C = 70$ °C	42	
	$T_A = 25$ °C	50 ^{b, c}	
	$T_A = 70$ °C	35 ^{b, c}	
Pulsed Drain Current	I_{DM}	180	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	2.25	A
	$T_A = 25$ °C	1.48 ^{b, c}	
Single Pulse Avalanche Current	I_{AS}	30	mJ
Single Pulse Avalanche Energy	E_{AS}	55	
Maximum Power Dissipation	$T_C = 25$ °C	2.7	W
	$T_C = 70$ °C	4.77	
	$T_A = 25$ °C	2.78 ^{b, c}	
	$T_A = 70$ °C	1.14 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c, d}	R_{thJA}	58	70	°C/W
Maximum Junction-to-Foot (Drain)	R_{thJF}	38	45	

Notes:

a. Package limited, $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. Maximum under Steady State conditions is 110 °C/W.

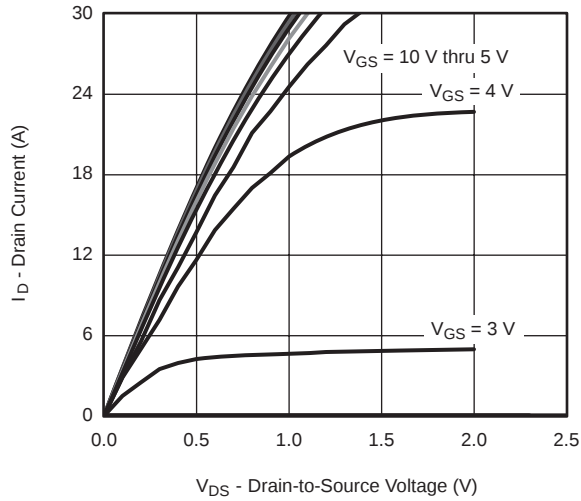
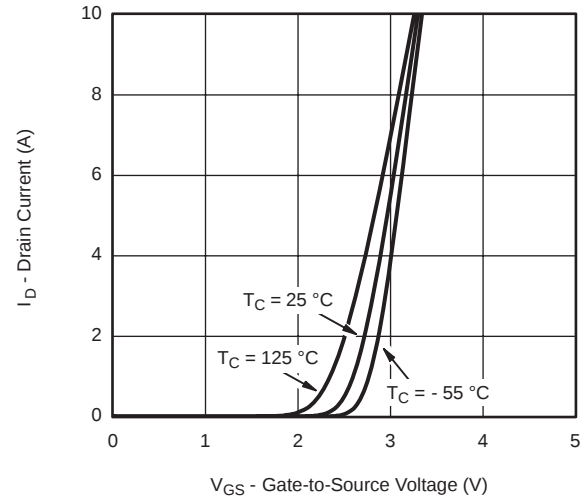
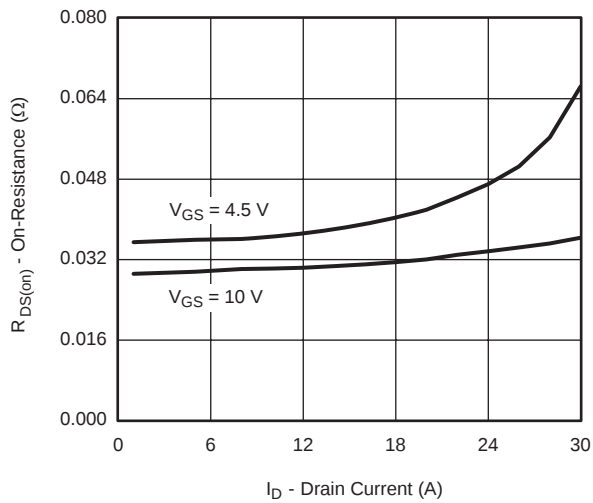
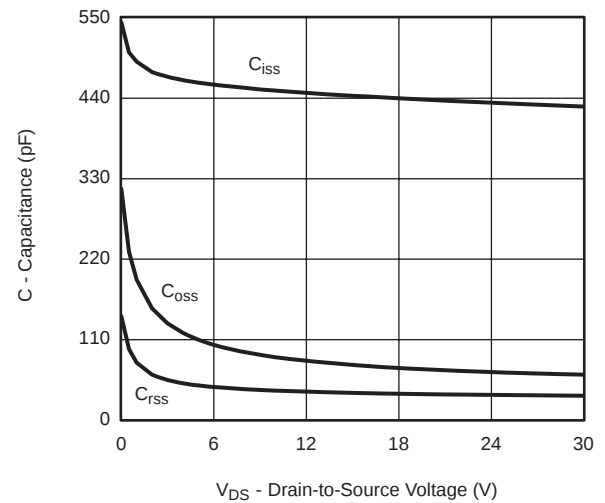
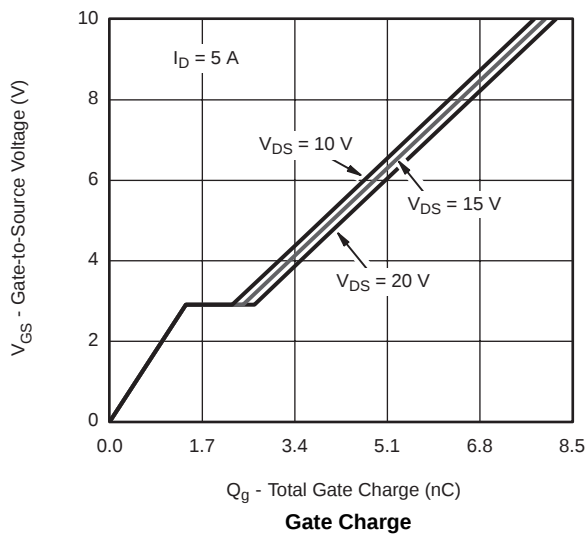
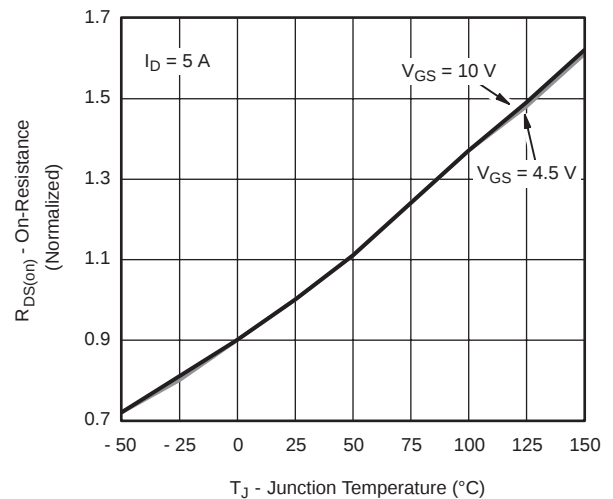
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		32		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.0		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A		0.0055		Ω
		V _{GS} = 4.5 V, I _D = 4 A		0.0065		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 5 A		16		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1000		pF
Output Capacitance	C _{oss}			217		
Reverse Transfer Capacitance	C _{rss}			155		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 5 A		15	25	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5 A		6.7	9.6	
Gate-Source Charge	Q _{gs}			4.4	6.0	
Gate-Drain Charge	Q _{gd}			3.05	4.0	
Gate Resistance	R _g	f = 1 MHz	0.8	4.3	8.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		12	24	ns
Rise Time	t _r			55	100	
Turn-Off Delay Time	t _{d(off)}			11	22	
Fall Time	t _f			8	16	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω		4	8	
Rise Time	t _r			9	18	
Turn-Off Delay Time	t _{d(off)}			10	20	
Fall Time	t _f			6	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			60	A
Pulse Diode Forward Current	I _{SM}				180	
Body Diode Voltage	V _{SD}	I _S = 2 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5 A, dI/dt = 100 A/μs, T _J = 25 °C		11	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}			4	8	nC
Reverse Recovery Fall Time	t _a			7		ns
Reverse Recovery Rise Time	t _b			4		

Notes:

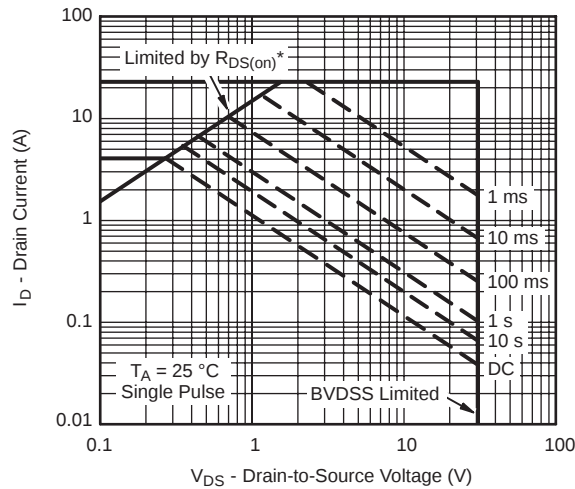
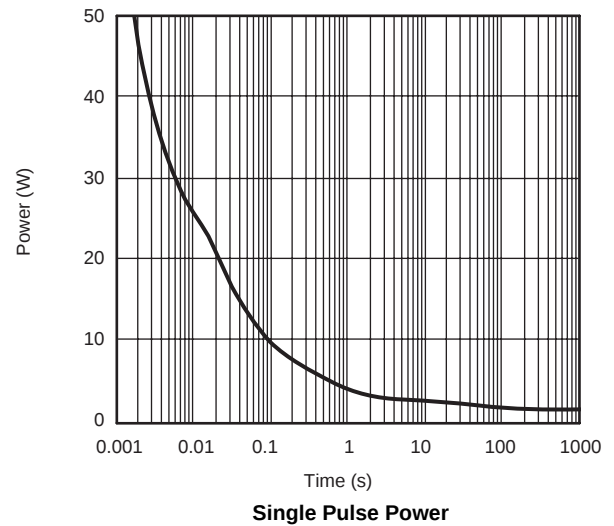
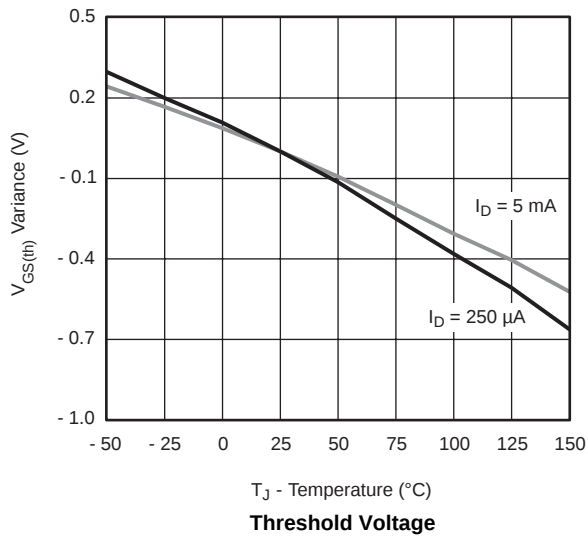
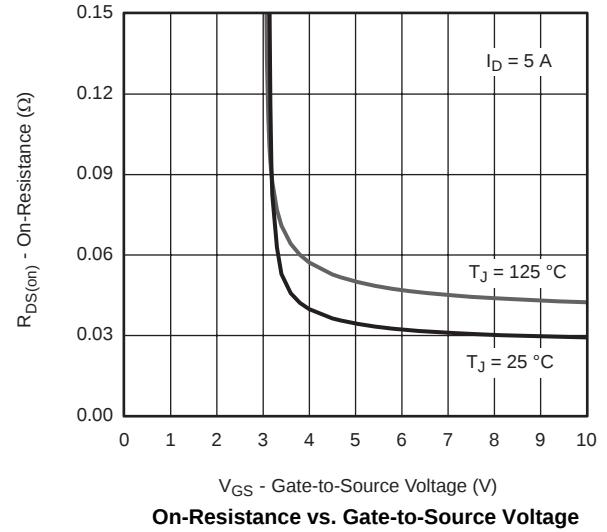
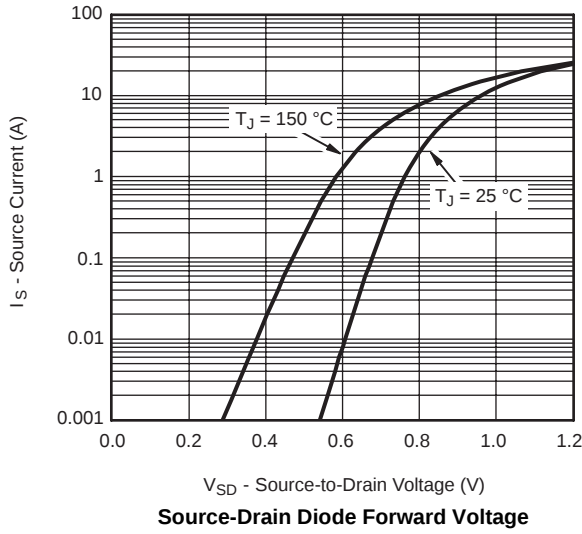
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

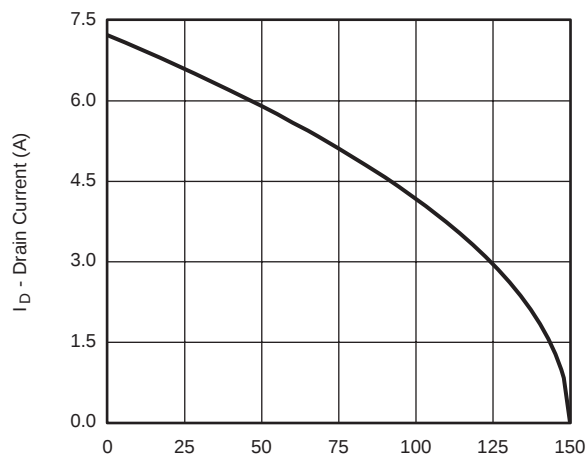
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

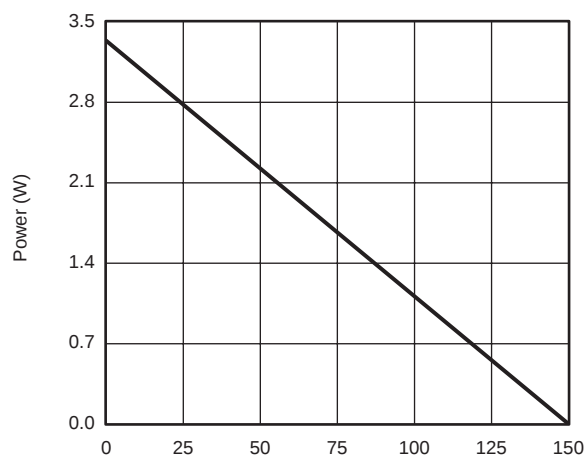


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

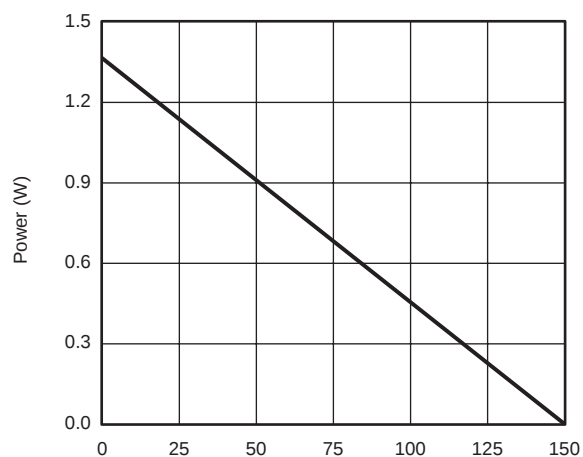
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


T_C - Case Temperature (°C)
Current Derating*



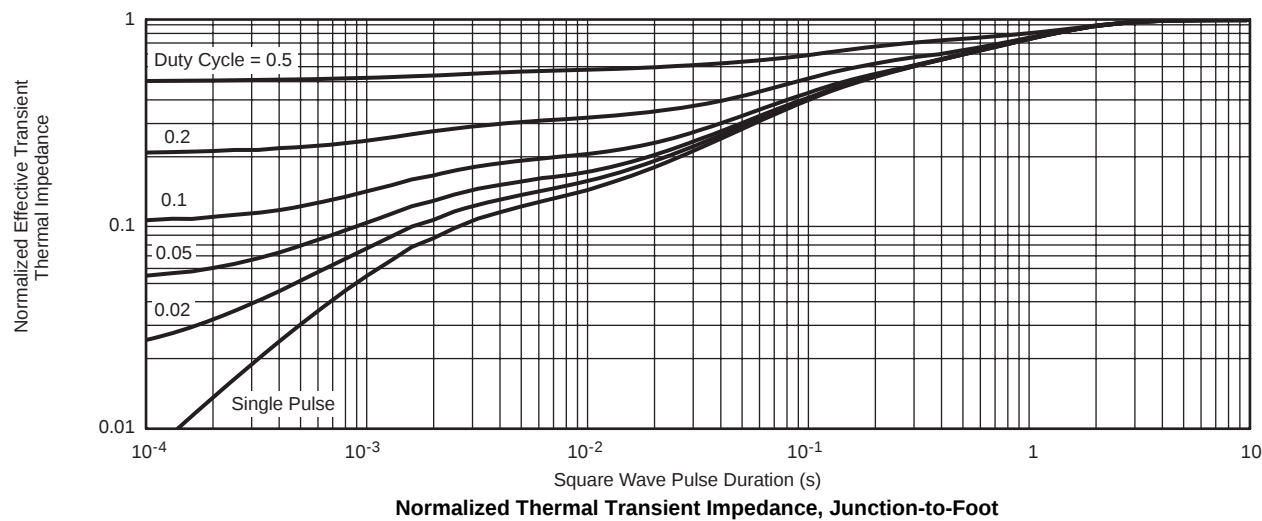
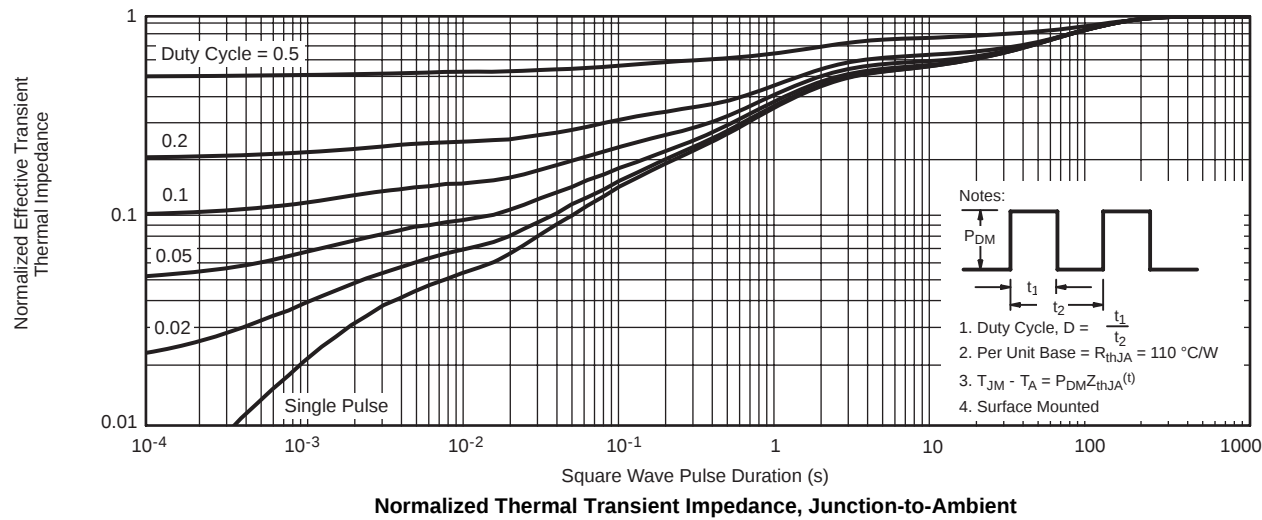
T_C - Case Temperature (°C)
Power, Junction-to-Foot



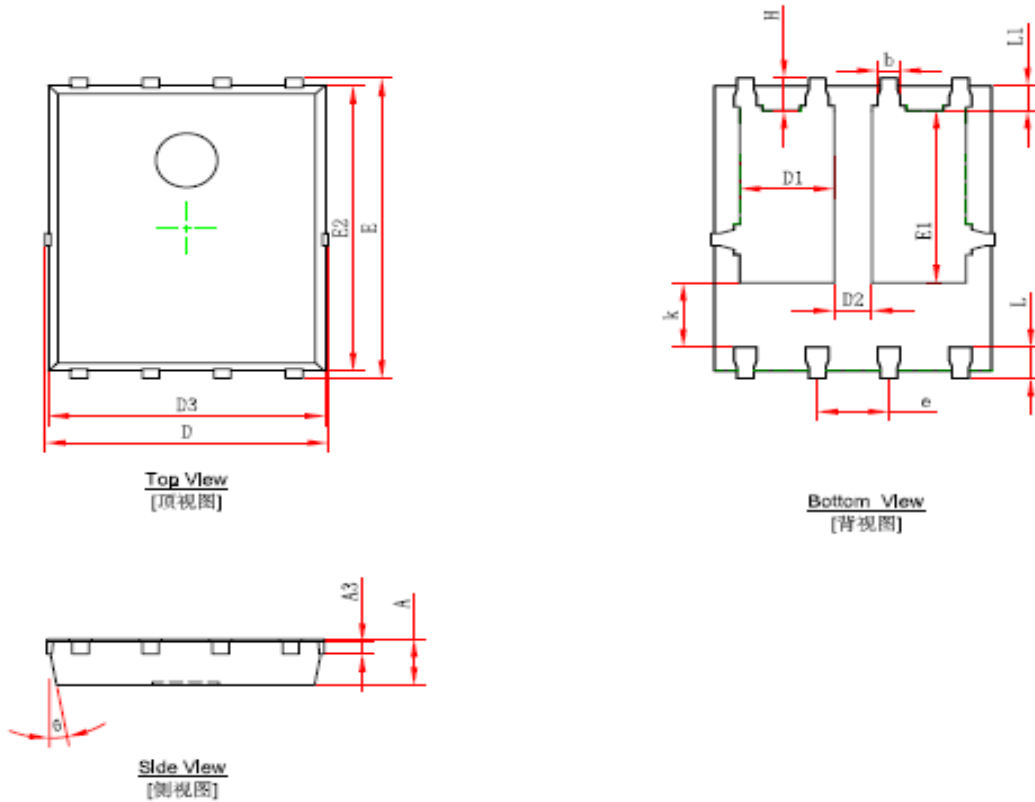
T_A - Ambient Temperature (°C)
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



PDFNWB5×6-8L-A PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254 REF.		0.010 REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270 TYP.		0.050 TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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